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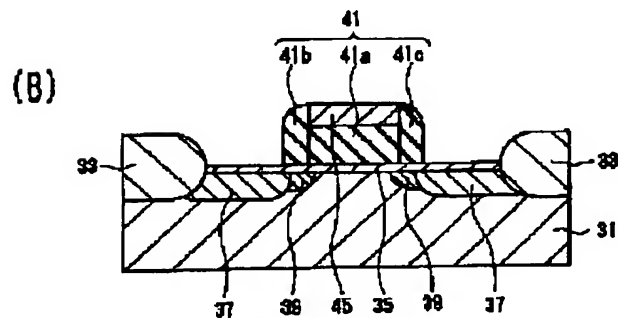
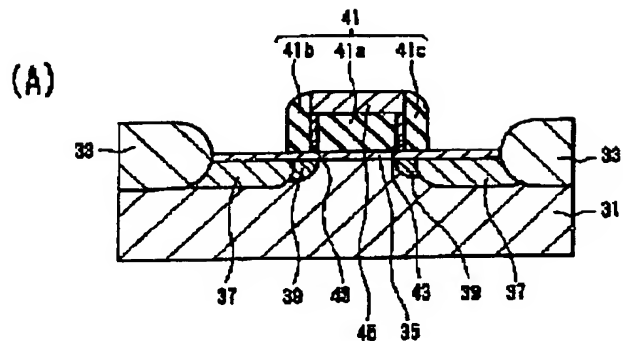
APPLICATION DATE : 12-02-92
APPLICATION NUMBER : 04025000

APPLICANT : OKI ELECTRIC IND CO LTD;

INVENTOR : MATSUHASHI HIDEAKI;

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TITLE : FIELD EFFECT TRANSISTOR



ABSTRACT : PURPOSE: To provide a field effect transistor (FET) which has an LDD structure, can reduce the increase in series resistance between a source and drain areas caused by an n^+ layer than the conventional FET and, is hardly deteriorated by hot carriers.

CONSTITUTION: A gate electrode 41 is constituted of three sections of a main gate section 41a made of a first material and two end gate sections 41b and 41c which are provided at both ends of the source and drain area sides of the gate section 41a and made of a second material. In addition, the first and second materials are selected so that the work function of the first material can become larger than that of the second material when the FET is of the N-channel or so that the work function of the first material can become smaller than that of the second material when the transistor is of the P-channel.

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